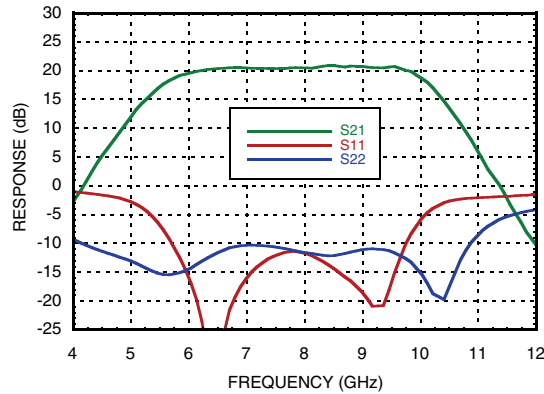
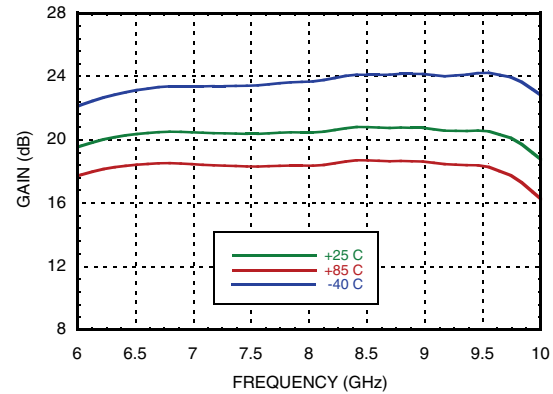


**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 6.0 - 9.5 GHz**

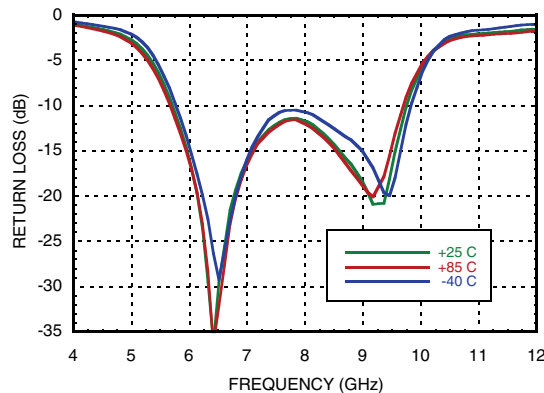
Broadband Gain & Return Loss



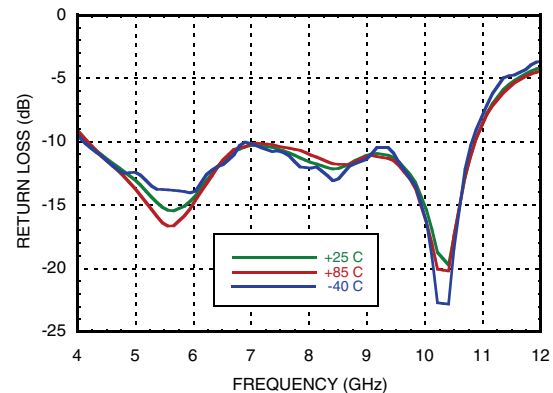
Gain vs. Temperature



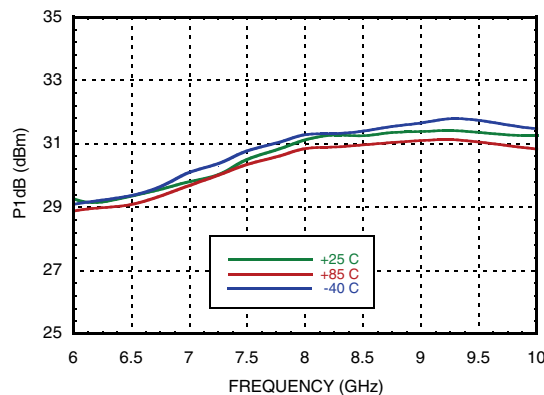
Input Return Loss vs. Temperature



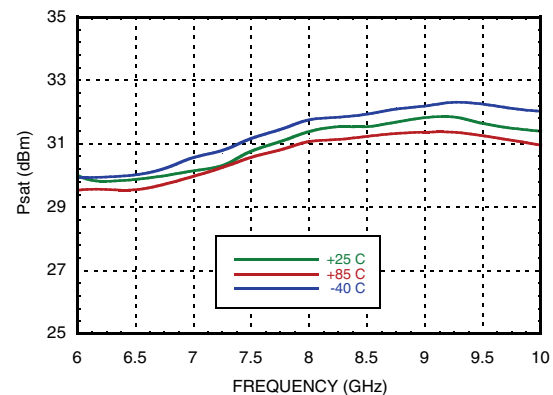
Output Return Loss vs. Temperature



P1dB vs. Temperature

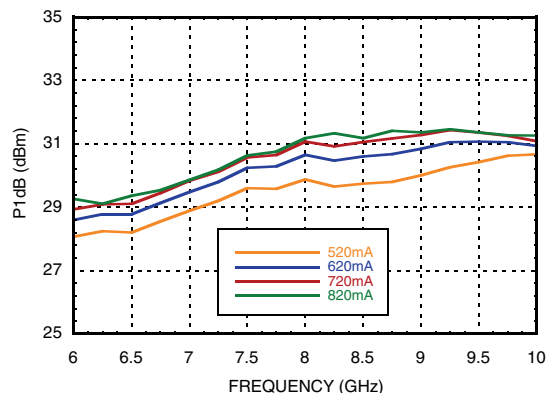


Psat vs. Temperature

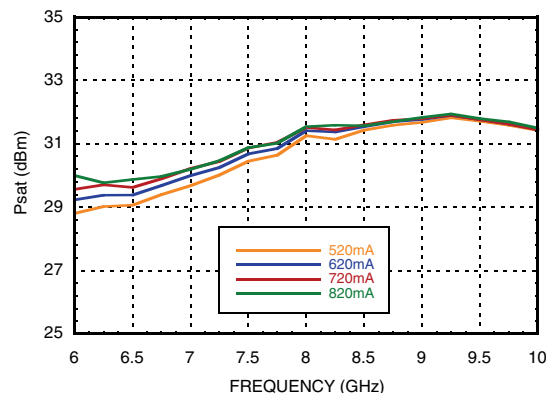


**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 6.0 - 9.5 GHz**

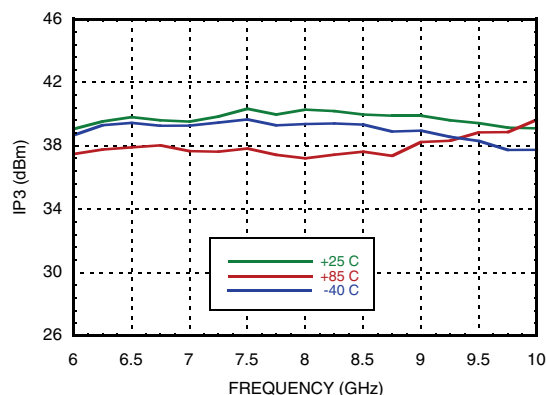
P1dB vs. Current



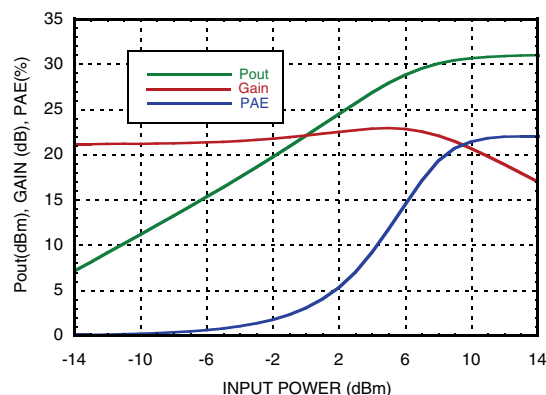
Psat vs. Current



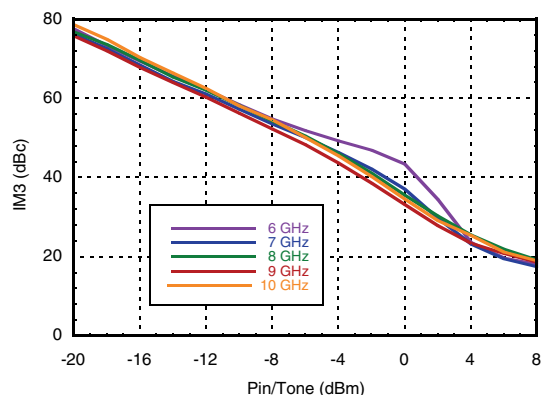
Output IP3 vs. Temperature
7V @ 520 mA, Pin/Tone = -15 dBm



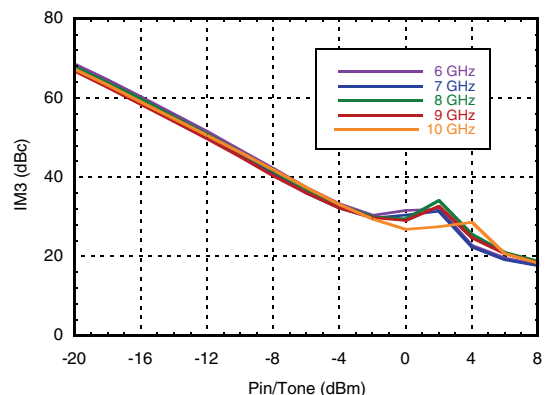
Power Compression @ 8 GHz,
7V @ 820 mA

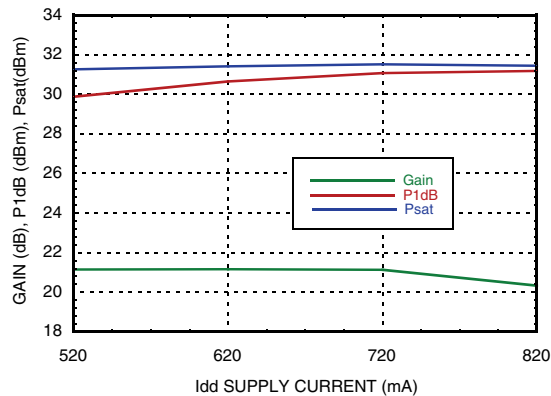
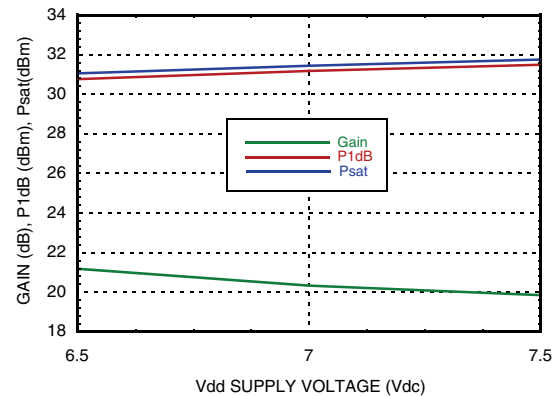
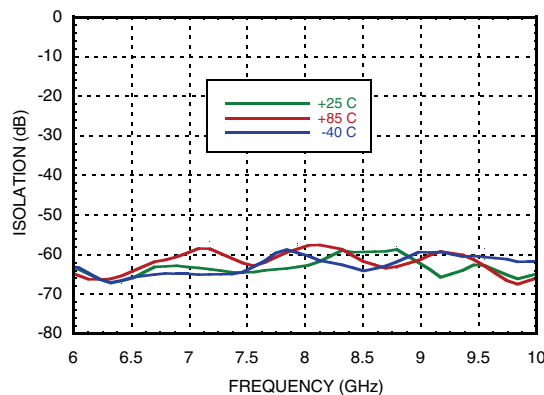
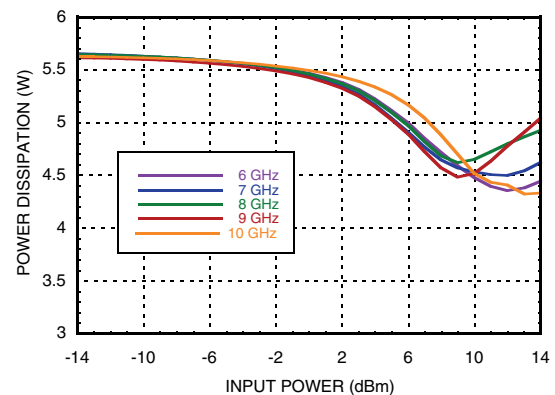


Output IM3, 7V @ 520 mA



Output IM3, 7V @ 820 mA



**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 6.0 - 9.5 GHz**
Gain & Power vs. Supply Current @ 8 GHz

Gain & Power vs. Supply Voltage @ 8 GHz

**Reverse Isolation
vs. Temperature, 7V @ 820 mA**

Power Dissipation

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+8 Vdc
Gate Bias Voltage (Vgg)	-2.0 to 0 Vdc
RF Input Power (RFIN)(Vdd = +7.0 Vdc)	+12 dBm
Channel Temperature	175 °C
Continuous Pdis (T= 75 °C) (derate 59.8 mW/°C above 75 °C)	5.98 W
Thermal Resistance (channel to package bottom)	16.72 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
ESD Sensitivity (HBM)	Class 0B. Passed 200V

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+6.5	824
+7.0	820
+7.5	815

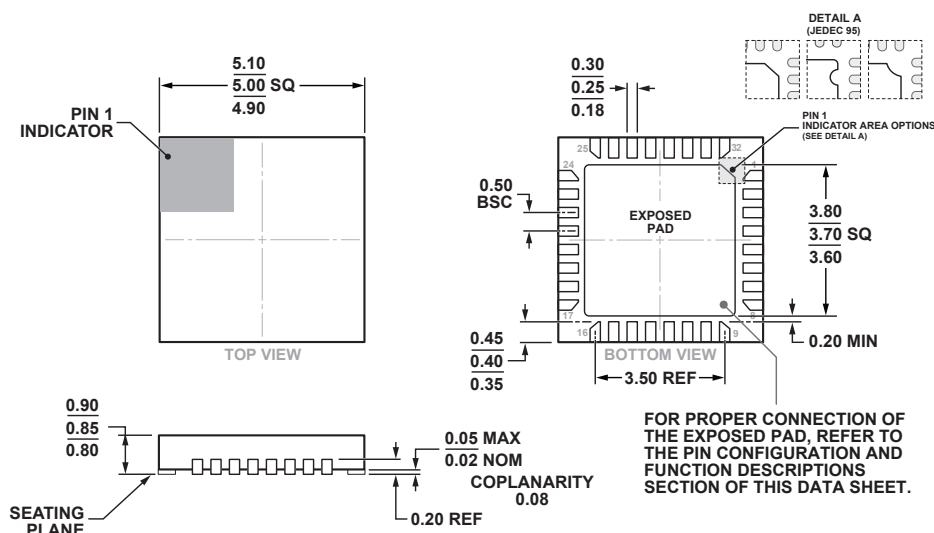
Note: Amplifier will operate over full voltage ranges shown above Vgg adjusted to achieve Idd = 820 mA at +7.0V



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 6.0 - 9.5 GHz**

Outline Drawing



COMPLIANT TO JEDEC STANDARDS MO-220-VHHD-4.

32-Lead Lead Frame Chip Scale Package [LFCSP]
5 mm × 5 mm and 0.90 mm Package Height
(HCP-32-3)
Dimensions shown in millimeters

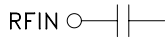
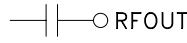
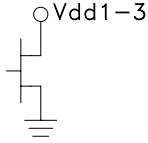
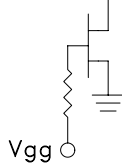
Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC590LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL3 ^[1]	H590 XXXX
HMC590LP5ETR	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL3 ^[1]	H590 XXXX

[1] Max peak reflow temperature of 260 °C

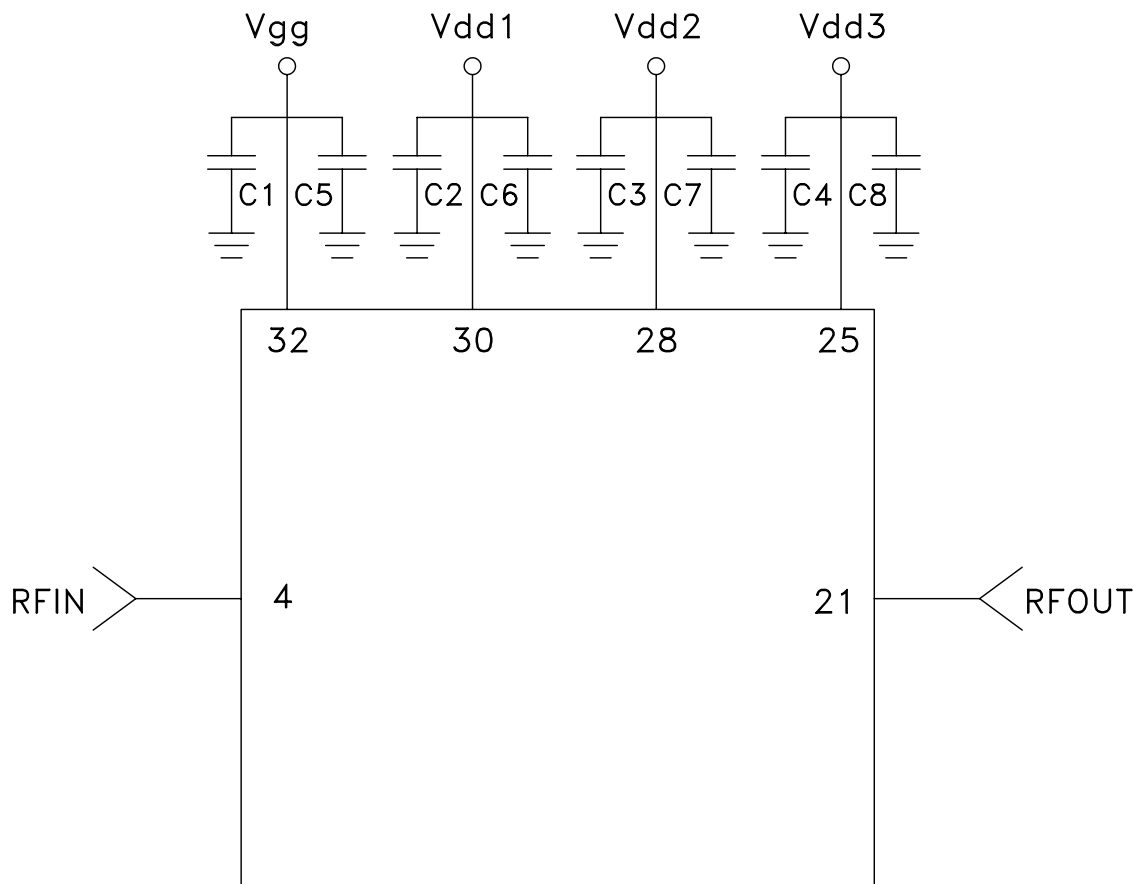
[2] 4-Digit lot number XXXX

**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 6.0 - 9.5 GHz**
Pin Descriptions

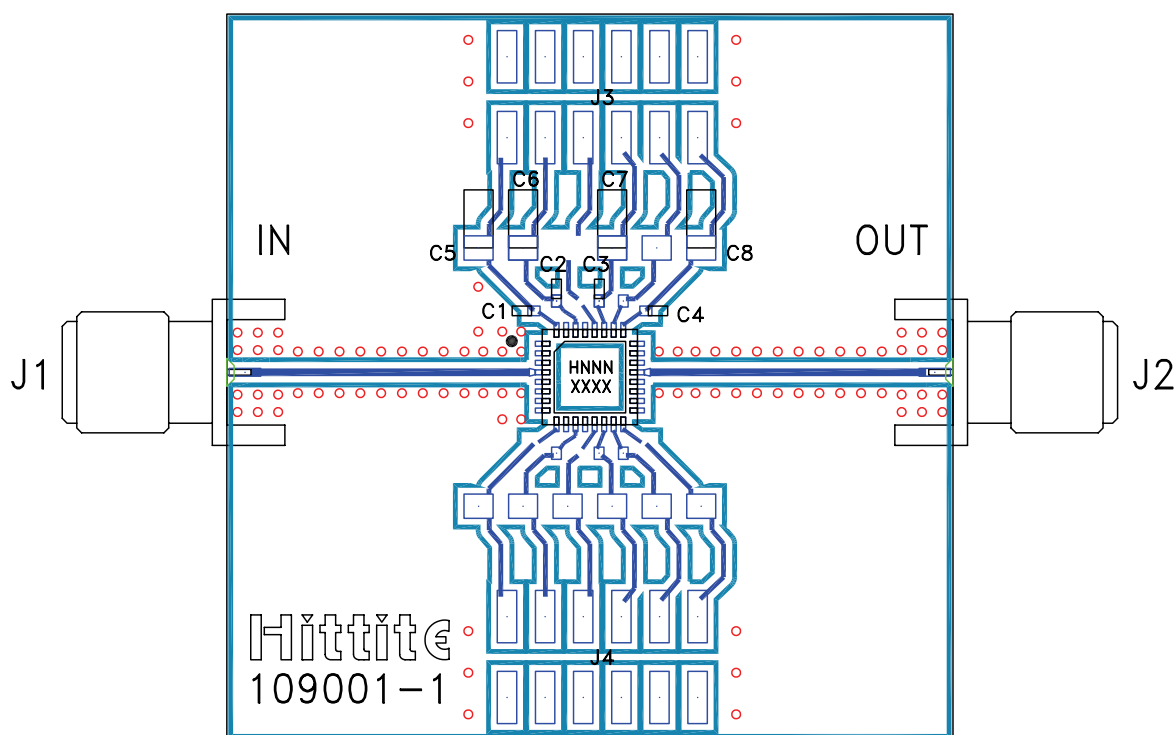
Pin Number	Function	Description	Interface Schematic
1, 2, 6 - 19, 23, 24, 26, 27, 29, 31	N/C	Not connected.	
3, 5, 20, 22	GND	These pins and package bottom must be connected to RF/DC ground.	
4	RFIN	This pad is AC coupled and matched to 50 Ohms.	
21	RFOUT	This pad is AC coupled and matched to 50 Ohms.	
25, 28, 30	Vdd 1-3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 2.2 μ F are required.	
32	Vgg	Gate control for amplifier. Adjust to achieve Idd of 820 mA. Please follow "MMIC Amplifier Biasing Procedure" Application Note. External bypass capacitors of 100 pF and 2.2 μ F are required.	

Application Circuit

Component	Value
C1 - C4	100pF
C5 - C8	2.2μF



Evaluation PCB



List of Materials for Evaluation PCB 115927-HMC590LP5 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3	DC Pin
C1 - C4	100 pF Capacitor, 0402 Pkg
C5 - C8	2.2 μ F Capacitor, 1206 Pkg
U1	HMC590LP5E
PCB [2]	109001 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices , Inc. upon request.